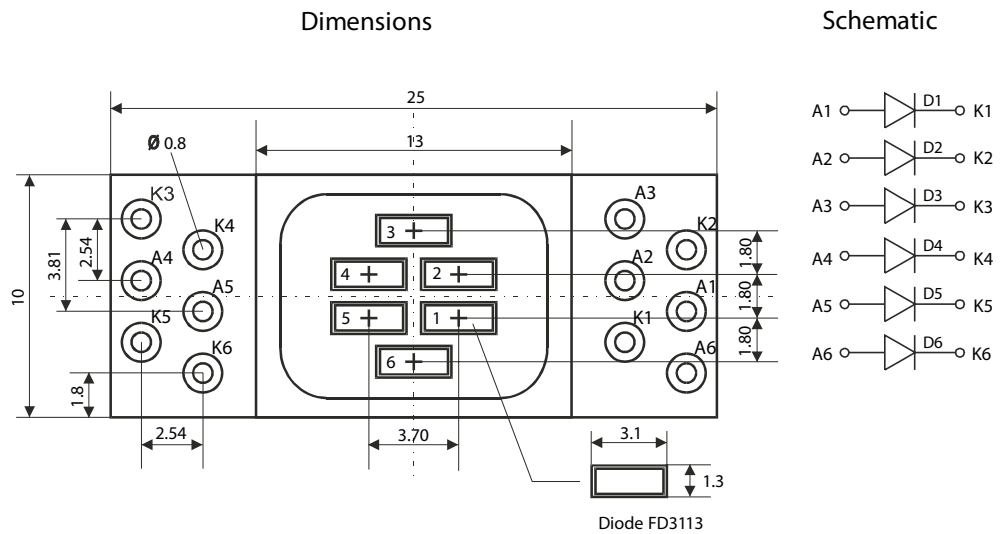


FEATURES

- High responsivity
- Low capacitance
- High reliability
- Peak wavelength at 830 nm

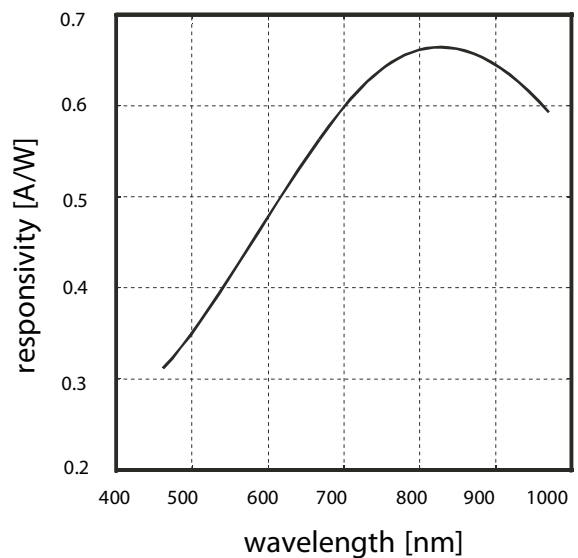


DESCRIPTION

The photosensor is made of 6-chip photodiode array. Photodiodes (FD3113) are produced in planar technology and passivated with silicon-nitride. Silicon-nitride is acting as antireflective layer. Photodiodes are bonded to the PCB and protected with transparent epoxy glue. The photodiode can work in photovoltaic or photoconductive mode.

TEMPERATURE CONDITIONS

Storage	0 °C...+70 °C
Operating	0 °C...+70 °C
Soldering	Hand soldering



PHOTODIODE CHARACTERISTICS

PRODUCT	DIMENSIONS		ELECTRICAL PARAMETERS				OPTICAL PARAMETERS		
			DARK CURRENT	BV	CAPACITANCE		PEAK	RESPONSE	CURRENT
TYPE	CHIP SIZE	ACTIVE AREA	$V_r = -5V$	$I_r > -50 \mu A$	$V_r = 0V$	$V_r = -5V$	I		
			TYP	MIN	TYP	TYP	TYP	TYP	TYP
			(nA)	(V)	(pF)	(pF)	(nm)	(A/W)	(μA)
FD 3113	3.1 x 1.3	3.10	<1	50	52	23	830	0.67	1000

Note 1: CURRENT (I_{sc}) is measured under 100 mW/cm² AM spectrum.